

TS-C2-311H-80DC

100G CFP2 ZR4 dual Rate

Features

- Supports 100GBASE-ZR4(100GE and OTU4);from 103.1Gb/s to 111.8Gb/s aggregate;
- Lane bit rate 25.78 Gb/s 100GE, 27.95 Gb/s OTU4;
- Up to 80km transmission on SMF;
- LANWDM laser and PIN receiver with SOA;
- High speed I/O electrical interface (CAUI-4);
- MDIO interface with integrated Digital Diagnostic monitoring;
- CFP2 MSA package with duplex LC connector;
- Single +3.3V power supply;
- Maximum power consumption 9W;
- Operating case temperature: 0 to +70 °C;
- Complies with IEEE802.3bm;
- Compliant to SFF-8665 and SFF-8679;
- Complies with EU Directive 2015/863/EU;

Application

- 100GBASE-ZR4;

Order Information

Table 1- order information

Part No.	Data Rate	Laser	Fiber Type	Distance	Optical Interface	Temp	DDMI
TS-C2-311H-80DC	103.1Gbps~111.8Gbps	LANWDM	SMF	80km	LC	0~70C	Y

Absolute Maximum Ratings

Table 2-Absolute Maximum Ratings

Parameter	Symbol	Min.	Typical	Max.	Unit	Notes
Storage Temperature	T _s	-40	-	+85	°C	
Supply Voltage	V _{CC}	-0.5	-	+4.0	V	
Operating Relative Humidity	RH	-	-	+85	%	

Recommended Operating Conditions

Table 3-Recommended Operating Conditions

Parameter	Symbol	Min.	Typical	Max.	Unit	Notes
Operating Case Temperature	T _c	0	-	+70	°C	

Power Supply Voltage	V _{CC}	3.13	3.3	3.47	V	
Power Supply Current	I _{CC}	-	-	2.59	A	
Maximum Power Dissipation	P _D	-	-	9	W	
Aggregate Bit Rate	BR _{AVE}	-	103.125	-	Gb/s	
Lane Bit Rate	BR _{LANE}	-	25.78	-	Gb/s	
Transmission Distance	TD		-	80	km	Over SMF with FEC

Optical Characteristics

Table 4-Optical Characteristics

Transmitter						
Parameter	Symbol	Min.	Typical	Max.	Unit	Notes
Center Wavelength Lane 0	λ_0	1294.53	1295.56	1296.59	nm	
Center Wavelength Lane 1	λ_1	1299.02	1300.05	1301.09	nm	
Center Wavelength Lane 2	λ_2	1303.54	1304.58	1305.63	nm	
Center Wavelength Lane 3	λ_3	1308.09	1309.14	1310.19	nm	
Total Launch Power, 100GE	P _{ALL}	-	-	12.5	dBm	1
Average Launch Power per Lane, 100GE	P _{TX_LANE}	1	-	6.5	dBm	1
Average Launch Power per Lane, OTU4	P _{TX_LANE}	0.6	-	6.5	dBm	1
Difference in launch power between lanes (OMA outer)	P _{TX_DELTA_LANE}	-	-	3	dB	
Average Output Power (Laser Turn off)	P _{OUT-OFF}	-	-	-30	dBm	
Side Mode Suppression Ratio	SMSR	30	-	-	dB	
Extinction Ratio, 100GE&OTU4	ER	8	-	-	dB	
Optical Eye Mask, 100GE&OTU4	{0.25, 0.4,0.45, 0.28, 0.28, 0.4}					2
Receiver						
Parameter	Symbol	Min.	Typical	Max.	Unit	Notes
Center Wavelength Lane 0	λ_0	1294.53	1295.56	1296.59	nm	
Center Wavelength Lane 1	λ_1	1299.02	1300.05	1301.09	nm	
Center Wavelength Lane 2	λ_2	1303.54	1304.58	1305.63	nm	
Center Wavelength Lane 3	λ_3	1308.09	1309.14	1310.19	nm	
Damage threshold, each lane	P _{damage}	5.5	-	-	dBm	
Average Rx Power per Lane, 100GE&OTU4	P _{RX_LANE}	-28		4.5	dBm	
OMA Sensitivity per Lane	P _{OMA_LANE}	-	-	-26	dBm	3

Notes:

1. The optical power is launched into SMF.
2. Measured with a PRBS 231-1 test pattern @25.78125/27.95 Gb/s, Hit ratio≤5E-5.
3. Measured with a PRBS 231-1 test pattern @25.78125/27.95 Gb/s, BER≤5E-5(Pre-FEC).

Electrical Characteristics

High-Speed Signal: Compliant to CAUI-4 (IEEE 802.3bm)

Low-Speed Signal: Compliant to CFP2 MSA Hardware

Specification Table 5-Electrical Characteristics

Transmitter (Module Input)						
Parameter	Symbol	Min.	Typical	Max.	Unit	Notes
Differential Data Input Amplitude	$V_{IN,P-P}$	85	-	900	mVpp	
Differential Termination Mismatch		-	10	-	%	
Tx_Disable	Normal Operation	V_{IL}	-0.3	-	0.8	V
	Laser Disable	V_{IH}	2	-	$V_{CC}+0.3$	V
Receiver (Module Output)						
Parameter	Symbol	Min.	Typical	Max.	Unit	Notes
Differential Data Output Amplitude	$V_{OUT,P-P}$	200	-	900	mVpp	
Differential Termination Mismatch (1MHZ)		-	10	-	%	
Output Rise/Fall Time, 20%~80%	T_R	12	-	-	ps	
Rx_LOS	Normal Operation	V_{OL}	-	-	0.2	V
	Lose Signal	V_{OH}	$V_{CC}-0.2$	-	-	V

Digital Diagnostics

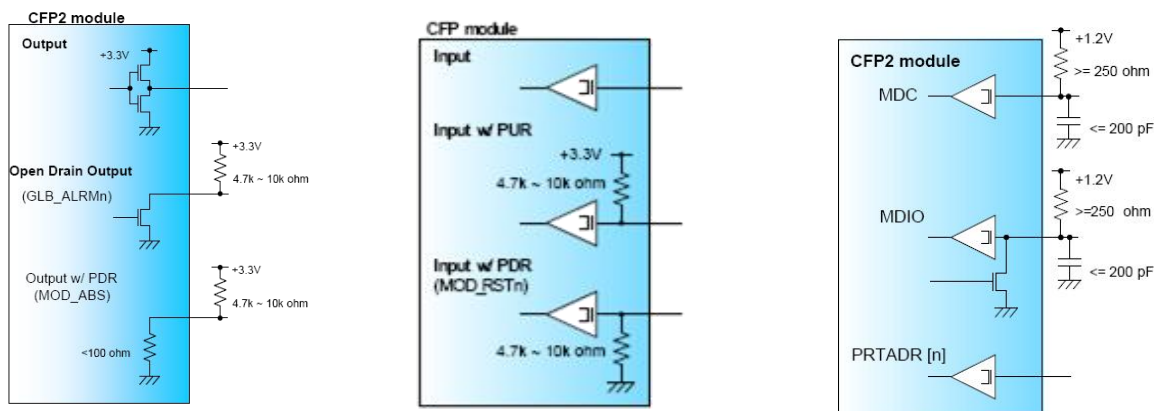
Table 6-Digital Diagnostics

Parameter	Range	Accuracy	Unit	Calibration
Temperature	-5 to 70	± 3	$^{\circ}\text{C}$	Internal
Voltage	0 to V_{CC}	$\pm 3\%$	V	Internal
Tx Bias Current Per Lane	0 to 100	$\pm 10\%$	mA	Internal
Tx Output Power Per Lane	1 to 6.5	± 3	dB	Internal
Rx Power (Each Lane)	-28 to 4.5	± 3	dB	Internal

Hardware Signal Pin Electrical Specification

Table 7-Reference 3.3V LVCOMS output/input termination

Reference MDIO Interface Termination



Note: The MSA recommends host termination resistor value of 560 Ohms, which provides the best balance of performance for both open-drain and active tri-state driver in the module.

Pin Definitions

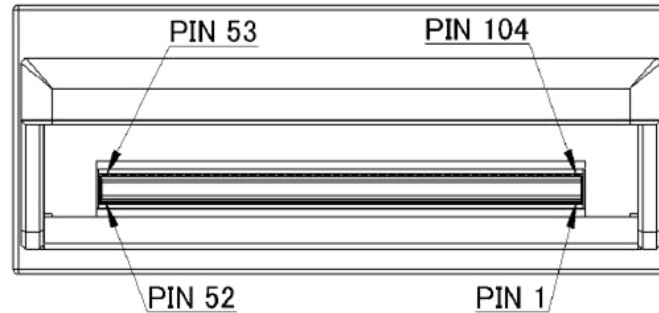
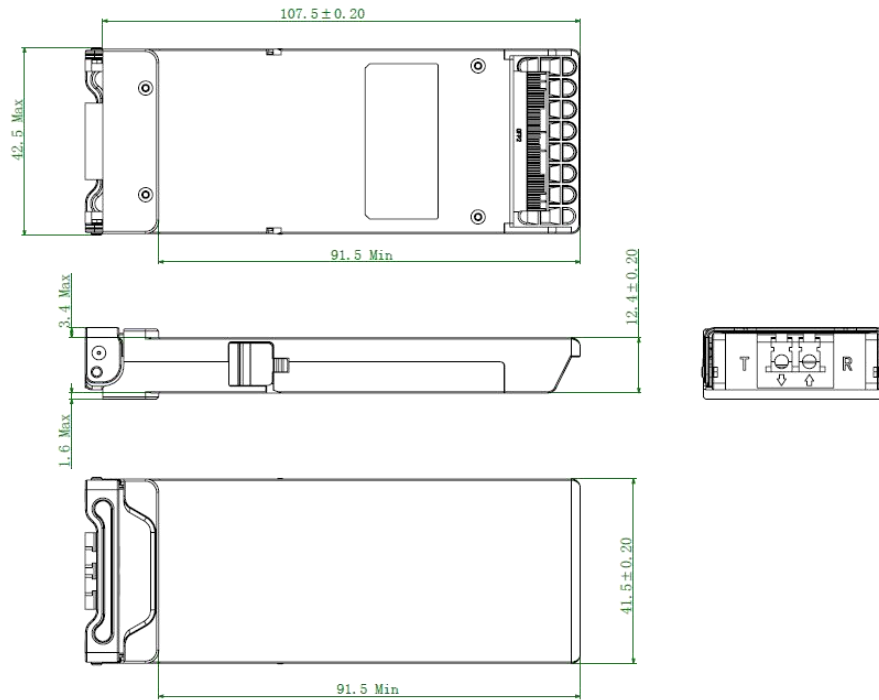


Table 8-Electrical Characteristics

Bottom (Nx25G)		Top (4x25G)	
1	GND	104	GND
2	(TX_MCLKn)	103	N.C.
3	(TX_MCLKp)	102	N.C.
4	GND	101	GND
5	N.C.	100	TX3n
6	N.C.	99	TX3p
7	3.3V_GND	98	GND
8	3.3V_GND	97	TX2n
9	3.3V	96	TX2p
10	3.3V	95	GND
11	3.3V	94	N.C.
12	3.3V	93	N.C.
13	3.3V_GND	92	GND
14	3.3V_GND	91	N.C.
15	VND_IO_A	90	N.C.
16	VND_IO_B	89	GND
17	PRG_CNTL1	88	TX1n
18	PRG_CNTL2	87	TX1p
19	PRG_CNTL3	86	GND
20	PRG_ALARM1	85	TX0n
21	PRG_ALARM2	84	TX0p
22	PRG_ALARM3	83	GND
23	GND	82	N.C.
24	TX_DIS	81	N.C.
25	RX_LOS	80	GND
26	MOD_LOPWR	79	(REFCLKn)
27	MOD_ABS	78	(REFCLKp)
28	MOD_RSTn	77	GND
29	GLB_ALARMn	76	N.C.
30	GND	75	N.C.
31	MDC	74	GND
32	MDIO	73	RX3n
33	PRTADR0	72	RX3p
34	PRTADR1	71	GND
35	PRTADR2	70	RX2n
36	VND_IO_C	69	RX2p
37	VND_IO_D	68	GND
38	VND_IO_E	67	N.C.
39	3.3V_GND	66	N.C.
40	3.3V_GND	65	GND
41	3.3V	64	N.C.
42	3.3V	63	N.C.
43	3.3V	62	GND
44	3.3V	61	RX1n
45	3.3V_GND	60	RX1p
46	3.3V_GND	59	GND
47	N.C.	58	RX0n
48	N.C.	57	RX0p
49	GND	56	GND
50	(RX_MCLKn)	55	N.C.
51	(RX_MCLKp)	54	N.C.
52	GND	53	GND

Mechanical Dimension



Warnings

Handling Precautions: This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures.

Laser Safety: Transcom transceiver uses a semiconductor laser system and is a laser class1 product acc. FDA, complies with 21CFR1040.10 and 1040.11. Also this product is a laser class1 product acc. IEC 60825-1.